

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	257/77,335,402,403,404,E29.027,E29.066,E29.256,E29.258,E29.261.ccls. and (SiC or (silicon near carbide)) and DMOS near (FET or transistor) and (impurity near concentration) with profile and @ad<"20050225"	US-PGPUB; USPAT	OR	ON	2009/08/13 11:59
L2	0	257/77,335,402,403,404,E29.027,E29.066,E29.256,E29.258,E29.261.ccls. and (SiC or (silicon near carbide)) and DMOS near (FET or transistor) and (impurity near concentration) with profile and @ad<"20050225"	US-PGPUB; USPAT; USOCR, FPRS, EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/13 12:00
S1	1089	257/77.ccls.	US-PGPUB; USPAT	OR	ON	2008/02/22 12:05
S2	72	257/77.ccls. and (impurity or dop \$3) with low near10 (surface or top)	US-PGPUB; USPAT	OR	ON	2008/02/22 12:08
S3	81	257/77.ccls. and (impurity or dop \$3) near3 profile	US-PGPUB; USPAT	OR	ON	2008/02/22 12:28
S4	11	257/77.ccls. and graded near8 (impurity or dop\$3) near3 profile	US-PGPUB; USPAT	OR	ON	2008/02/22 12:29
S5	35	257/77.ccls. and drift adj layer near10 epitaxial	US-PGPUB; USPAT	OR	ON	2008/02/22 15:40
S6	0	single adj step near5 ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:29
S7	17	single adj step near5 ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:29
S8	28	single adj step with ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:33
S9	28	(single adj step or single-step) with ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:33
S10	2	"20040119076"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:13
S11	1	(silicon adj carbide or epitaxial) with (single-step or single adj step) near5 ion near implant\$5 and implantation adj energy and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:20
S12	13	(single-step or single adj step) near5 ion near implant\$5 and implantation adj energy and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:31

S13	20	constant near5 implantation adj energy and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:37
S14	10	accumulation same mobility near10 (improv\$3 or increas\$3) and silicon adj carbide and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2009/01/07 17:56
S15	4	("20040238883" "6228725" "6455892" "6784492").FN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/01/07 18:17
S16	450	257/335,548,549,e21.056,e21.054,e21.065.ccls. and ((impurity or dopant or doping) near10 (profile or gradient or vary\$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS)	US-PGPUB; USPAT	OR	ON	2009/07/28 17:49
S17	70	257/335,548,549,e21.056,e21.054,e21.065.ccls. and ((impurity or dopant or doping) near10 (profile or gradient or vary\$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	US-PGPUB; USPAT	OR	ON	2009/07/28 17:50
S18	1	10/588103	US-PGPUB; USPAT	OR	ON	2009/07/28 18:07
S19	9	("4487639" "4868626" "4881119" "4935799" "5065213" "5118635" "5247200" "5380670" "5424231").FN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/28 19:05
S20	0	257/335,548,549,e21.056,e21.054,e21.065.ccls. and ((impurity or dopant or doping) near10 (profile or gradient or vary\$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/28 19:10

S21	14	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/28 19:10
S22	14	S21 not S17	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/28 19:10
S23	590	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	US-PGPUB; USPAT	OR	ON	2009/07/28 19:13
S24	589	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high near concentration or highly near concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	US-PGPUB; USPAT	OR	ON	2009/07/28 19:14
S25	571	S24 not S17	US-PGPUB; USPAT	OR	ON	2009/07/28 19:14

S26	50	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high near concentration or highly near concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC) near8 epitaxial	US-PGPUB; USPAT	OR	ON	2009/07/28 19:15
S27	44	S26 not S17	US-PGPUB; USPAT	OR	ON	2009/07/28 19:15
S28	3	(miura-mineo.in, or rohm.as.) and ((metal adj oxide adj semiconductor or MOS or MOSFET) and (silicon adj carbide or SiC) and channel with (low\$2 or high\$2) with (impurity or dopant))	US-PGPUB; USPAT	OR	ON	2009/07/28 19:26
S29	11	("20020038891" "20020172774" "20040036113" "20040119076" "20040159886" "4827319" "5976936" "6020600" "6373102" "6573534" "6639273").PN.	US-PGPUB; USPAT	OR	ON	2009/07/28 19:27
S31	1	"6573534".pn.	US-PGPUB; USPAT	OR	ON	2009/07/29 12:04
S32	21	("4859621" "5170231" "5233215" "5323040" "5389799" "5396085" "5399515" "5451797" "5459107" "5460985" "5506421" "5514604" "5543637" "5574295" "5614749" "5629531" "5681762" "5723376" "5773849" "5776837" "6020600").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/29 12:10
S33	1	(nonuniformly near doped or non-uniformly near3 concentration) and @ad<"20050225" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC) near8 epitaxial	US-PGPUB; USPAT	OR	ON	2009/07/29 12:59
S34	128	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or retrograde)) and @ad<"20050225" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC) near8 epitaxial	US-PGPUB; USPAT	OR	ON	2009/07/29 13:01

S35	1	"6455892".pn.	US-PGPUB; USPAT	OR	ON	2009/08/07 11:53
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EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S30	8	((metal adj oxide adj semiconductor or MOS or MOSFET) and (silicon adj carbide or SiC) and channel with (low\$2 or high\$2) with (impurity or dopant)).clm.	US-PGPUB	OR	ON	2009/07/28 19:23

8/13/2009 12:01:42 PM

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